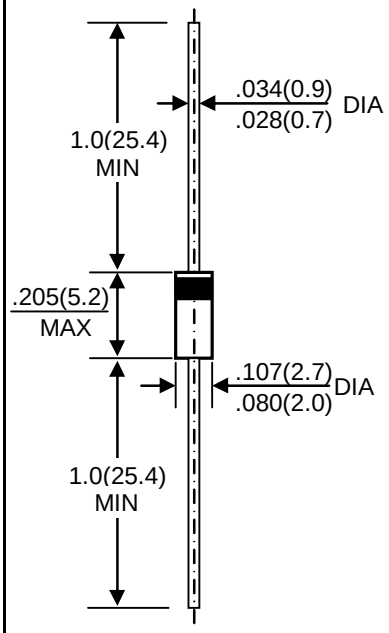
SILICON BIDIRECTIONAL DIACS	POWER DISSIPATION **150** mW

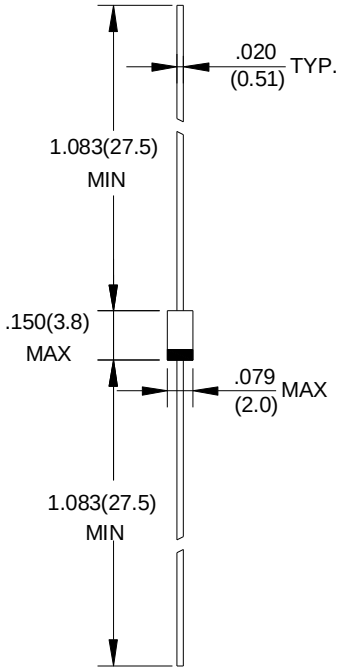
FEATURES

- Three way layer two terminal, axial lead , hermetically sealed diacs are designed specifically for triggering thyrisitors .The demonstrate low breakover current. The breakover symmetry is within three volts(DB3,DB4) or four volts(DB6).These diacs are intended for use in thyrisitors phase control.,circuits for lamp dimming universal motor speed control and heat control
- This diocle is also avaiable in the DO-41case.

DO- 41



DO-35(GLASS)



Dimensions in inches and (millimeters)

ABSOLUTE RATINGS

PARAMETERS	SYMBOL	VALUE			UNITS
		DB3	DB4	DB6	
Power Dissipation on Printed Cir cuit(L=10mm) T_A=50℃	Pc	150			mW
Repetitive Peak on-state Current Tp=10uS f=100Hz	I_{TRM}	2.0			A
Storage and Operating Juntion Temperature	T_{STG}/T_J	-44 to+125/-40 to+110			℃

ELECTRICAL CHARACTERISTICS

PAPRAMETERS	SYMBOLS	TEST CONDITIONS		VALUE			UNITS
				DB3	DB4	DB6	
Breakover Voltage*	V_{BO}	C=22nf** See Diagram 1	Min	28	35	56	V
			Typ	32	40	60	
			Max	36	45	70	
Breakover Voltage Symmetry	$1+V_{BO}I-1-V_{BO}I$	C=22nf** See Diagram 1	Max	±3			V
Dynamic Breakover Voltage	1±△V1	△I=(I_{BO} to IF=10mA) See FIG 1	Min	5			V
Output Voltage*	V_O	See FIG 2	Min	5			V
Breakover Current*	I_{BO}	C=22nf**	Max	100			uA
Rise Time*	tr	See FIG 3	Typ	1.5			uS
Leakage Current*	I_B	I_B=0.5 V_{BO} MAX See FIG 3	Max	10			uA

NOTE:* Electrical characteristics applicable in both forward and reverse directions.

** Connected in parallel with the devices.

FIG.1-CURRENT-VOLTAGE CHARACTERISTICS

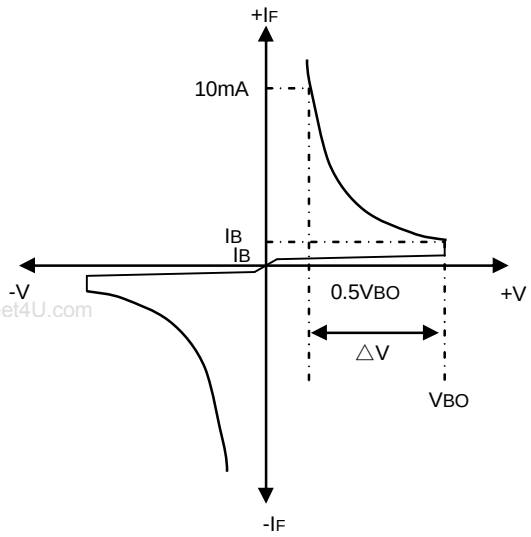


FIG.2-TEST CIRCUIT FOR OUTPUT VOLATGE

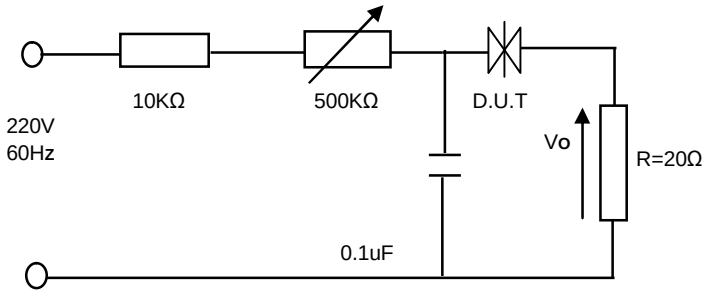


FIG.3-TEST CIRCUIT SEE FIG.2 ADJUST R
FOR Ip=0.5A

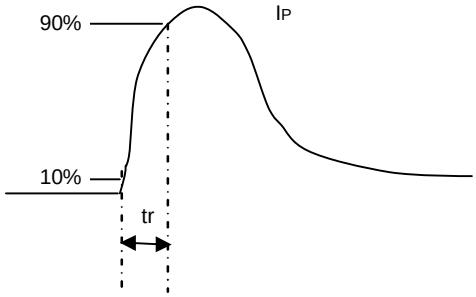


FIG.4-TEST CIRCUIT FOR OUTPUT

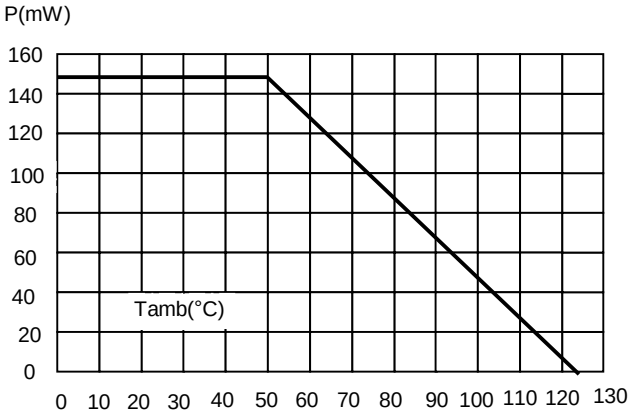


FIG.5-RELATIVE VARIATION OF VBO VERSUS
JUNCTION TEMPERATURE(TYPICAL VALUES)

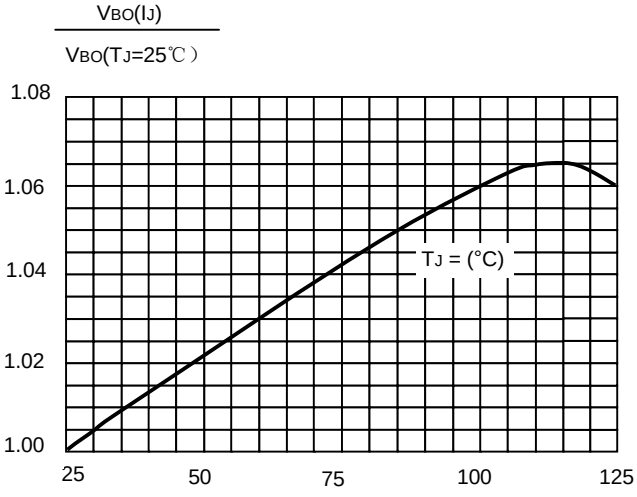


FIG.6-PEAK PULSE CURRENT VERSUS PULSE
DURATION (MAXIMUM VALUES)